

Application No.: 10/712,236

Docket No.: JCLA11795

**In The Specification:**

Please amend paragraph [0033] as follows:

[0033] Note that the second conductive type doped region 210 of each diode 203 is coupled to the second conductive type doped region 206 and the first conductive type doped region 208 of the following diode 203. With this setup, ~~the emitter (the first conductive type doped region 208) and the base (the second conductive type doped region 206) of~~ since, in the same diode 203, the second conductive type doped region 206 is voltage equivalent to the first conductive type doped region 208, a parasitic bipolar junction transistor 216, constructed by the emitter (the first conductive type doped region 208), the collector (the substrate 200) and the base (the second conductive type doped region 206), within the substrate 200 ~~are non-conductive is turned off~~. Hence, conduction between the emitter (the first conductive type doped region 208) and the collector (the substrate 200) of the parasitic bipolar junction transistor 216 is also prevented thereby resolving the current leak problem of conventional diodes.

Please amend paragraph [0042] as follows:

[0042] Note that the diode structure according to this invention still includes a parasitic bipolar junction transistor 316 within the substrate 300. However, ~~the base (the second conductive type doped region 306) and the emitter (the first conductive type doped region 308) of the parasitic bipolar junction transistor 316 do not conduct because the base is at a voltage higher than (or equal to) the emitter~~ the base (the second conductive type doped region 306) is at a

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voltage higher than (or equal to) the emitter (the first conductive type doped region 308).  
Therefore, the parasitic bipolar junction transistor 316 possesses the base, the collector and the  
emitter is turned off. Hence, conduction between the emitter (the first conductive type doped region 308) and the collector (the substrate 300) of the parasitic bipolar junction transistor 316 is also prevented thereby resolving the current leak problem of conventional diodes.

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